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**AO2301**

P-Channel Enhancement-Mode MOS FETs

[www.sot23.com.tw](http://www.sot23.com.tw)

### Features

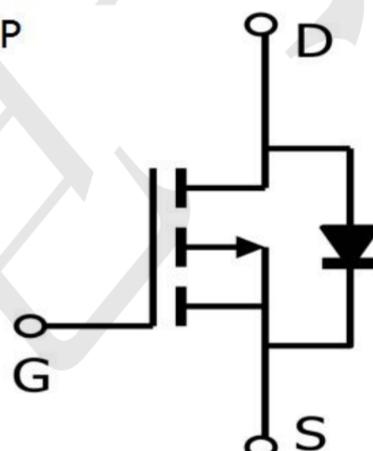
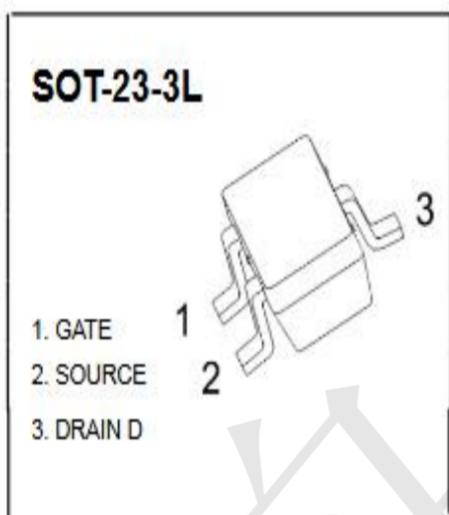
- -20 V -3A **RDS(on)MAX**
- 90mΩ -4 5V  
115mΩ@-2.5V
- SOT23-3L

### Applications

- Load Switch for Portable Devices
- DC/DC Converter

### Ordering Information

Part Number	Qty per Reel	Reel Size
A02301	3000	7"



### Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	-20	V
Gate-Source Voltage	V <sub>GSS</sub>	±12	
Continuous Drain Current	I <sub>D</sub>	-3	A
Pulsed Diode Current	I <sub>DM</sub>	-15	
Continuous Source-Drain Current(Diode Conduction)	I <sub>S</sub>	-0.8	
Power Dissipation	P <sub>D</sub>	1.25	W
Thermal Resistance from Junction to Ambient ( $t \leq 5\text{s}$ )	R <sub>θJA</sub>	150	°C/W
Operating Junction	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>STG</sub>	-55~+150	°C



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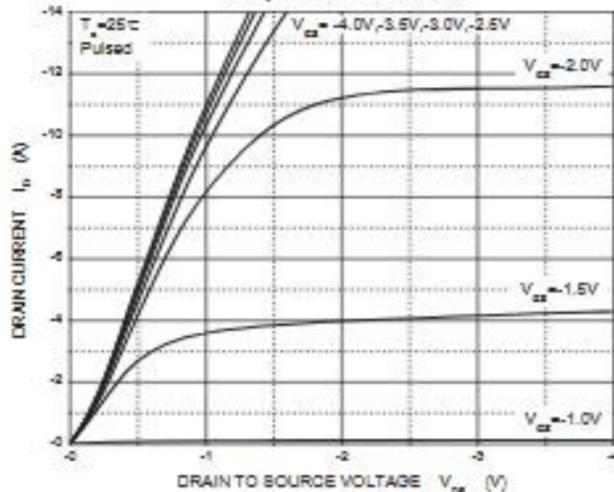
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**Electrical Characteristics ( $T_A=25^\circ\text{C}$  unless otherwise specified)**

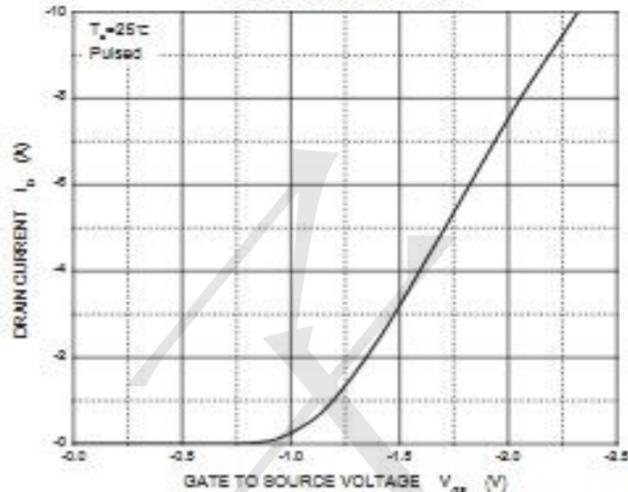
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static</b>						
Drain-source breakdown voltage	V(BR)DSS	VGS = 0V, ID = -250μA	-20			V
Gate-source threshold voltage	VGS(th)	VDS = VGS, ID = -250μA	-0.4		-1.	V
Gate-source leakage	IGSS	VDS = 0V, VGS = ±12V			±100	nA
Zero gate voltage drain current	IDSS	VDS = -20V, VGS = 0V			-1	μA
Drain-source on-state resistancea	RDS(on)	VGS = -4.5V, ID = -3A		66	90	mΩ
		VGS = -2.5V, ID = -2A		83	115	mΩ
Forward transconductancea	gfs	VDS = -4.5V, ID = -3A		4		S
Diode forward voltage	VSD	IS=-1A,VGS=0V		-0.8	-1.3	V
<b>Dynamic</b>						
Input capacitance	Ciss	VDS = -16V, VGS = 0V, f=1MHz		589		pF
Output capacitance	Coss			92		pF
Reverse transfer capacitanceb	Crss			68		pF
Total gate charge	Qg	VDS = -16V, VGS = -4.5V, ID = -3A		5.5	10	nC
Gate-source charge	Qgs			0.8		nC
Gate-drain charge	Qgd			1.3		nC
Gate resistance	Rg	f=1MHz		6		Ω
<b>Switchingb</b>						
Turn-on delay time	td(on)	VDD= -10V RL=6Ω, ID ≈ -3A, VGEN= -4.5V, Rg=6Ω		10	20	ns
Rise time	tr			35	60	ns
Turn-off delay time	td(off)			30	50	ns
Fall time	tf			10	20	ns
<b>Drain-source body diode characteristics</b>						
Continuous Source-Drain Diode Current	IS	Tc=25°C			-1.3	A
Pulsed Diode forward Current	ISM				-20	A



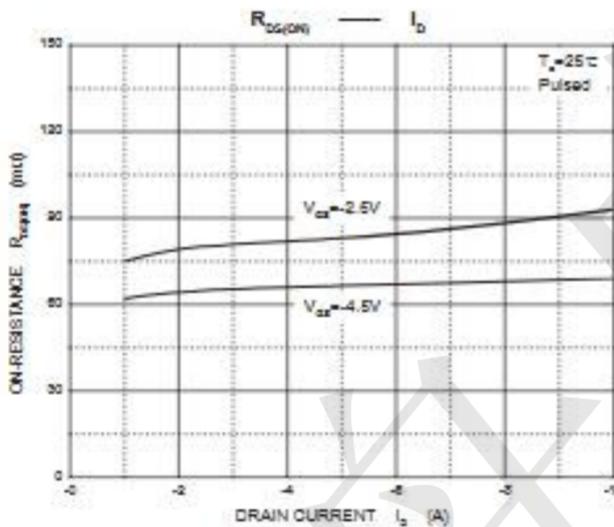
Output Characteristics



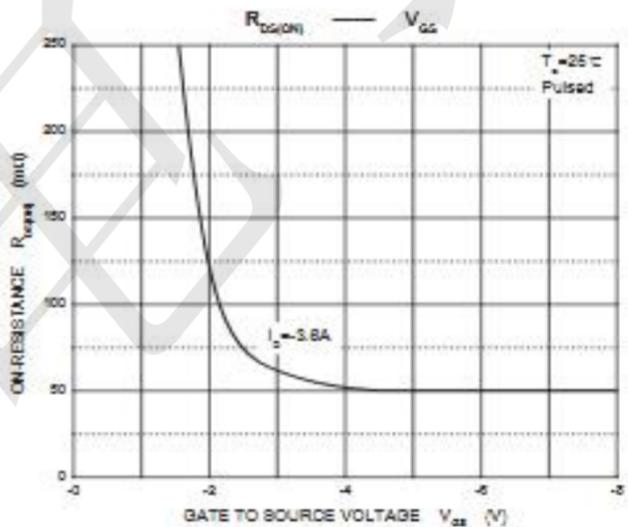
Transfer Characteristics



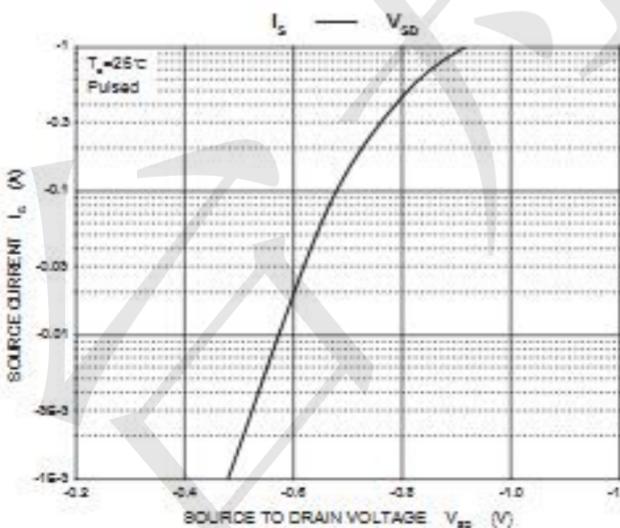
$R_{DS(on)}$  —  $I_D$



$R_{DS(on)}$  —  $V_{GS}$



$I_S$  —  $V_{SD}$





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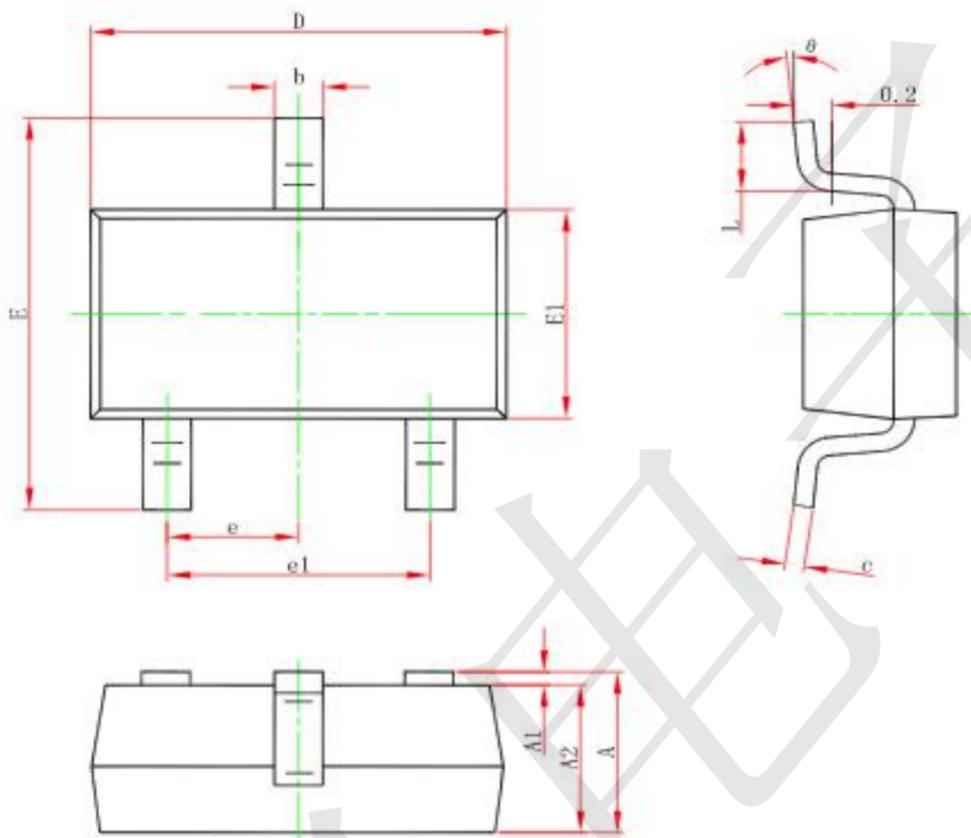
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SOT-23-3L PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°